

NPN Transistor

350mW SOT-23 AEC-Q101

MMBTA42-A

MERITEK

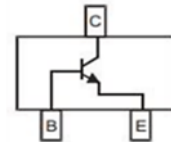
FEATURE

- Silicon Planar Design for High Voltage Application
- Collector-Emitter Voltage $V_{CE}=300V$
- Collector Current: $I_C=500mA$
- Application: Switching and High Voltage Amplifier
- AEC-Q101 Qualified



MECHANICAL DATA

- Case: SOT-23, Molded Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026



MAXIMUM RATING

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_{tot}	350	mW
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 ~+150	°C

ELECTRICAL CHARACTERISTICS

Parameter- ON Characteristic	Conditions	Symbol	Min.	Max.	Unit
DC Current Gain	$V_{CE}=10V, I_C=1mA$	h_{FE}	25	-	-
	$V_{CE}=10V, I_C=10mA$		80	200	
	$V_{CE}=10V, I_C=30mA$		40	-	
Collector-Emitter Saturation Voltage	$I_C=20mA, I_B=2mA$	$V_{CE(SAT)}$	-	0.5	V
Base-Emitter Saturation Voltage	$I_C=20mA, I_B=2mA$	$V_{BE(SAT)}$	-	0.9	V
Parameter- OFF Characteristics	Conditions	Symbol	Min.	Max.	Unit
Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	$V_{(BR)CBO}$	300	-	V
Collector-Emitter Breakdown Voltage	$I_C=1.0mA, I_B=0$	$V_{(BR)CEO}$	300	-	V
Emitter-Base Breakdown Voltage	$I_E=100\mu A, I_C=0$	$V_{(BR)EBO}$	6	-	V
Base Cut-Off Current	$V_{CB}=200V, I_E=0$	I_{CBO}	-	100	nA
Emitter Cut-Off Current	$V_{EB}=6V, I_C=0$	I_{EBO}	-	100	nA
Collector Capacitance	$V_{CB}=20.0V, I_E=0, f=1MHz$	C_{ob}	-	3	pF
Parameter-Small Signal	Conditions	Symbol	Min.	Max.	Unit
Current-Gain – Bandwidth Product	$I_C=10mA, V_{CE}=20V, f=100MHz$	f_T	50	-	MHz

Note:

1. $T_A=25^\circ C$ unless otherwise noted.

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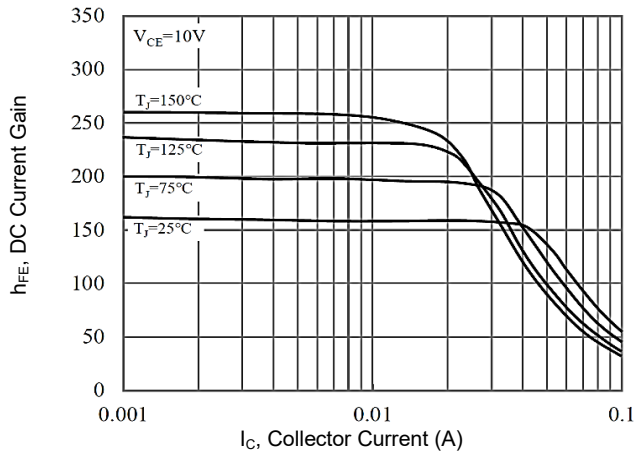
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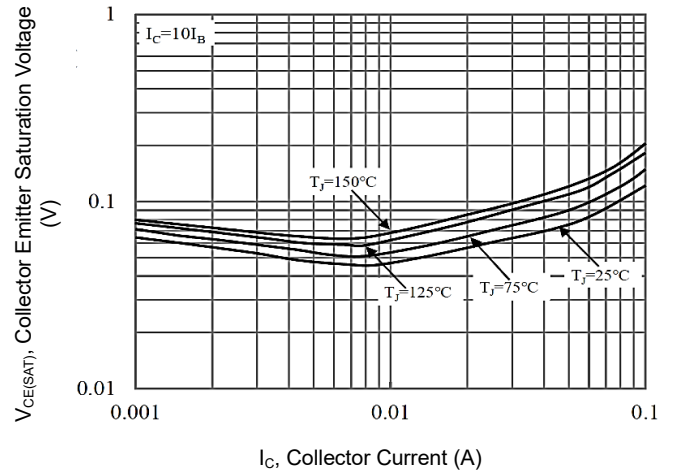
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CHARACTERISTIC CURVES

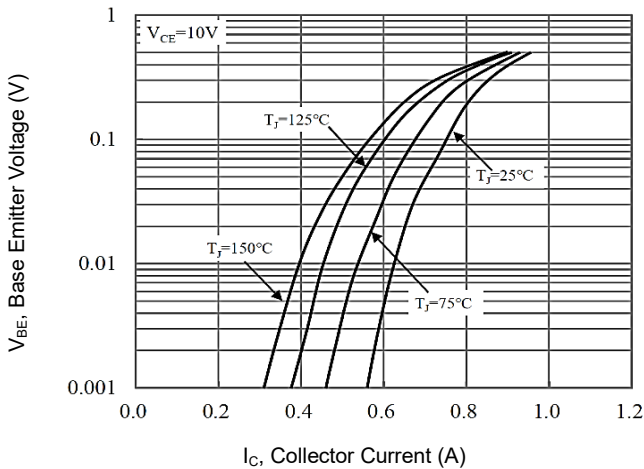
DC Current Gain



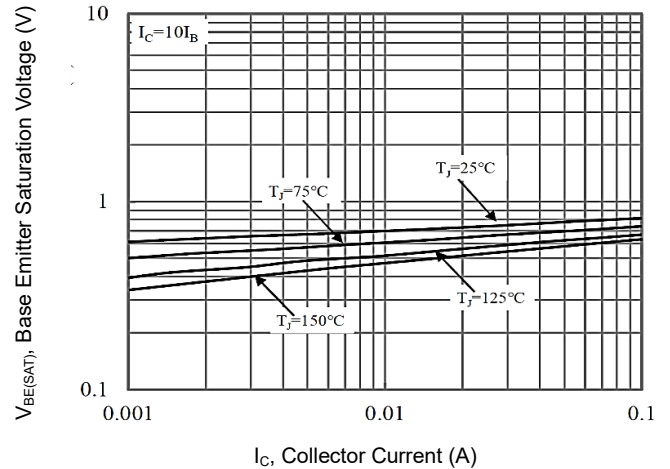
Collector Emitter Saturation Voltage



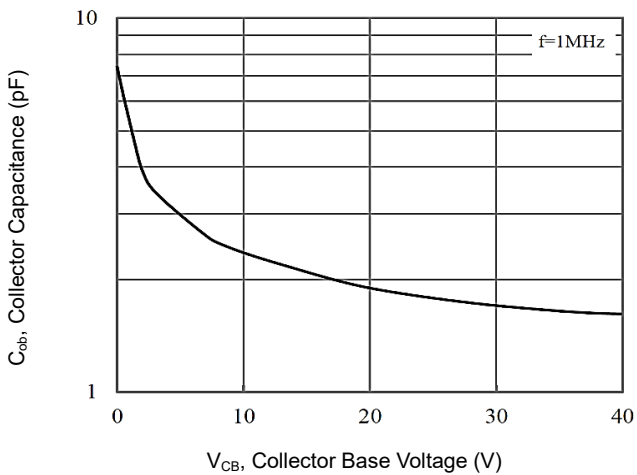
Base Emitter On Voltage



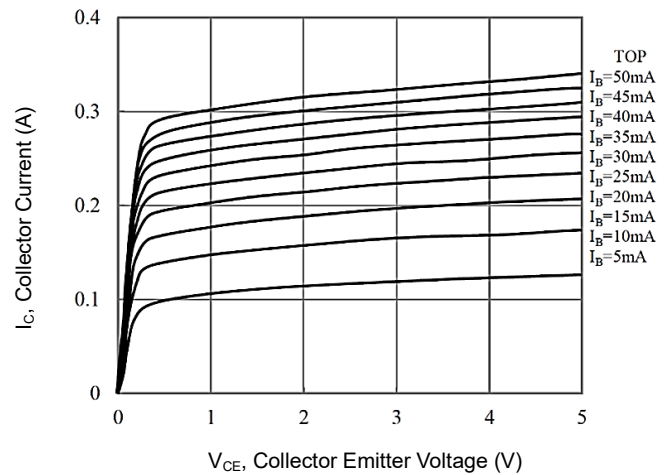
Base Emitter Saturation Voltage



Capacitance



Collector-Emitter Voltage vs. Collector Current



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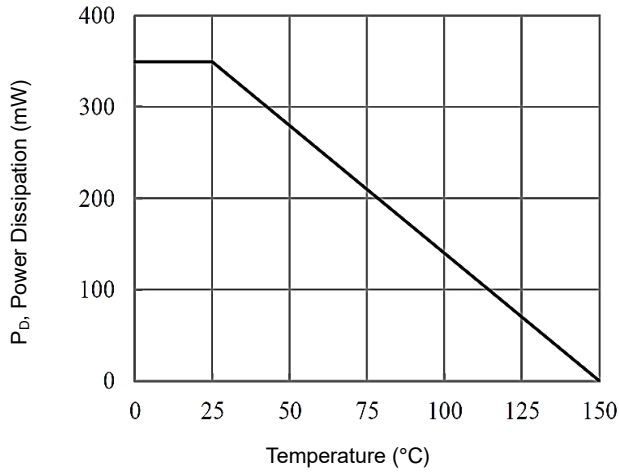
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CHARACTERISTIC CURVES

Power Derating Curves



DIMENSIONS

SOT-23	Min (mm)	Max (mm)
A1	0.00	0.10
A2	0.79	1.40
b	0.30	0.50
c	0.08	0.20
D	2.70	3.10
e	0.89	1.02
e1	1.78	2.04
E	2.10	2.80
E1	1.20	1.60
L	0.15	--
X	0.80	
X1	0.95	
Y	1.00	
Y1	1.00	
Y2	3.00	

